

11ES1 - 11ES2

SILICON RECTIFIER DIODES

PRV : 100 - 200 Volts

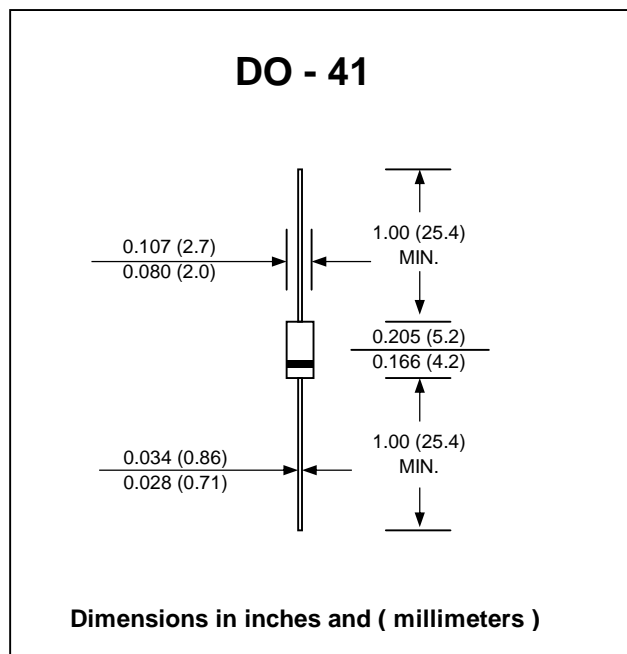
Io : 1.0 Ampere

FEATURES :

- * High current capability
- * High surge current capability
- * High reliability
- * Low reverse current
- * Low forward voltage drop
- * **Pb / RoHS Free**

MECHANICAL DATA :

- * Case : DO-41 Molded plastic
- * Epoxy : UL94V-O rate flame retardant
- * Lead : Axial lead solderable per MIL-STD-202, Method 208 guaranteed
- * Polarity : Color band denotes cathode end
- * Mounting position : Any
- * Weight : 0.339 gram



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.
 Single phase, half wave, 60 Hz, resistive or inductive load.
 For capacitive load, derate current by 20%.

RATING	SYMBOL	11ES1	11ES2	UNIT
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	100	200	Volts
Maximum RMS Voltage	V _{RMS}	70	140	Volts
Maximum DC Blocking Voltage	V _{DC}	100	200	Volts
Maximum Average Forward Current Ta = 50°C	I _F	1.0		Amp.
Maximum Peak Forward Surge Current	I _{FSM}	45		Amps.
Maximum Forward Voltage at I _F = 1.0 Amp.	V _F	1.0		Volts
Maximum DC Reverse Current at rated DC Blocking Voltage	I _{RM}	50		μA
Junction Temperature Range	T _J	- 65 to + 175		°C
Storage Temperature Range	T _{STG}	- 65 to + 175		°C

RATING AND CHARACTERISTIC CURVES (11ES1 - 11ES2)

FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

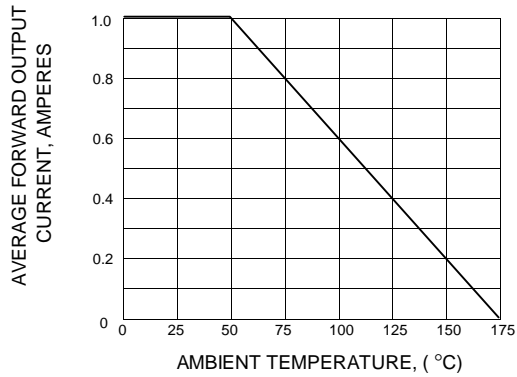


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

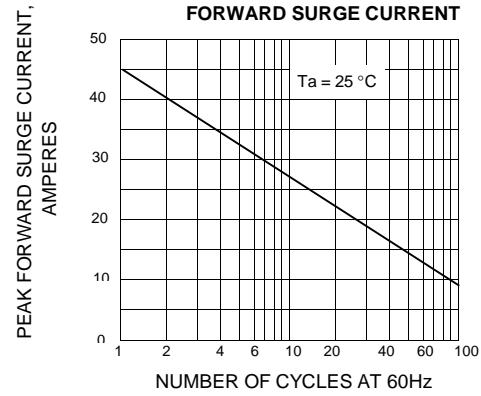


FIG.3 - TYPICAL FORWARD CHARACTERISTICS

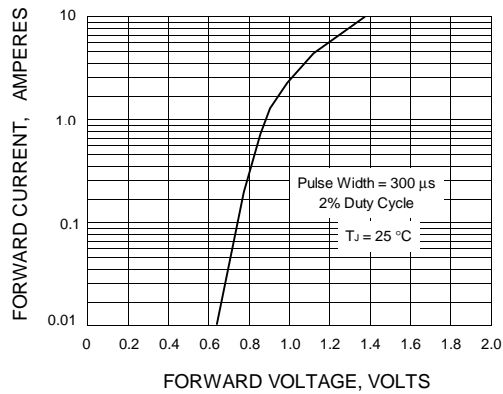


FIG.4 - TYPICAL REVERSE CHARACTERISTICS

